

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a circuit block formed on a semiconductor substrate; and

5 a shield comprising a lower metal layer, an upper metal layer and an interlayer insulation film disposed between the lower metal layer and the upper metal layer, the shield covering the circuit block.

2. The semiconductor device of claim 1, wherein the circuit block comprises a

10 circuit which includes at least a resistor, a transistor or a capacitor.

3. The semiconductor device of claim 1, further comprising a wiring line connected to the circuit block, wherein the wiring line extends outside of the shield through a window formed in a side wall of the shield.

15 4. The semiconductor device of claim 1, wherein at least the lower metal layer or the upper metal layer is configured to a part of a metal layer that is formed to be a part of the semiconductor device other than the shield.

20 5. The semiconductor device of claim 1, further comprising another shield of a different height.

6. The semiconductor device of claim 1, wherein the shield comprises an outside wall and an inside wall disposed inside the outside wall, wherein a metal portion of the inside
25 wall is disposed to cover an insulation portion of the outside wall.

7. A semiconductor device comprising:

a circuit block formed on a semiconductor substrate; and

30 a shield comprising a lower metal layer, an upper metal layer and an interlayer insulation film disposed between the lower metal layer and the upper metal layer, the shield

covering the circuit block; and

an intermediate metal layer disposed inside the shield.

8. The semiconductor device of claim 7, wherein the plane of the intermediate metal
5 layer also includes within the shield the interlayer insulation film, and the surface area of the
intermediate metal layer is larger than the surface area of the insulation film of said plane
within the shield.

9. The semiconductor device of claim 7, wherein the shield comprises an outside
10 wall and an inside wall disposed inside the outside wall, wherein a metal portion of the inside
wall is disposed to cover an insulation portion of the outside wall.

10. A semiconductor device comprising:
a first circuit block formed on a semiconductor substrate;
15 a second circuit block formed on the semiconductor substrate; and
a shield comprising a top portion made of a metal and covering only the first circuit
block, the top portion being configured to be at a ground potential.

11. The semiconductor device of claim 10, wherein the entire shield is made of the
20 metal.

12. The semiconductor device of claim 10, wherein the shield comprises a side wall
that includes a part of the top portion, a metal portion and an insulation portion disposed at
least between the part of the top portion and the metal portion.

25 13. The semiconductor device of claim 12, wherein the top portion and the metal
portion is electrically connected.

14. The semiconductor device of claim 10, further comprising an insulation body
30 filling in the inside of the shield.

15. The semiconductor device of claim 12, wherein the side wall comprises an outside wall and an inside wall disposed inside the outside wall, wherein the metal portion of the inside wall is disposed to cover the insulation portion of the outside wall.